# MCH3376

# ON Semiconductor®

# Power MOSFET −20V, 241mΩ, −1.5A, Single P-Channel

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#### **Features**

- · ESD diode-Protected gate
- · High speed switching and Low loss
- · Pb-free and RoHS Compliance
- · Drive at low voltage: 1.8V drive
- · Low RDS(on)

# **Specifications**

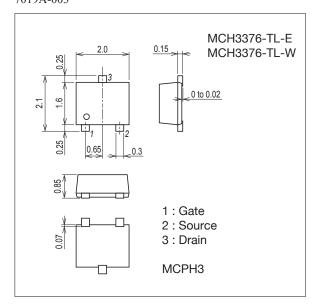
#### **Absolute Maximum Ratings** at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-1.5	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-6	Α
Power Dissipation	PD	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	0.8	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### **Package Dimensions**

unit : mm (typ) 7019A-003

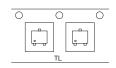


# **Product & Package Information**

• Package : MCPH3

JEITA, JEDEC : SC-70, SOT-323
Minimum Packing Quantity : 3,000 pcs./reel

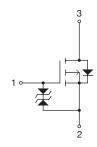
### **Packing Type: TL**



#### Marking



#### **Electrical Connection**



#### ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

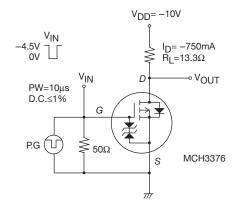
## MCH3376

#### **Electrical Characteristics** at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Parameter		Conditions	min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-20			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V			-1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ
Gate Threshold Voltage	V <sub>GS</sub> (th)	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA -0.4			-1.4	V
Forward Transconductance	9FS	V <sub>DS</sub> =-10V, I <sub>D</sub> =-750mA	V <sub>DS</sub> =-10V, I <sub>D</sub> =-750mA 1.14			S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	ID=-750mA, VGS=-4.5V		185	241	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =-300mA, V <sub>GS</sub> =-2.5V		275	385	mΩ
	R <sub>DS</sub> (on)3	I <sub>D</sub> =-100mA, V <sub>GS</sub> =-1.8V		410	615	mΩ
Input Capacitance	Ciss			120		pF
Output Capacitance	Coss	V <sub>DS</sub> =-10V, f=1MHz		26		pF
Reverse Transfer Capacitance	Crss			20		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			5.3		ns
Rise Time	t <sub>r</sub>	On a serial Frank Olympulk		9.7		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		16		ns
Fall Time	tf			14		ns
Total Gate Charge	Qg			1.7		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =-10V, V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-1.5A		0.28		nC
Gate-to-Drain "Miller" Charge	Qgd			0.47		nC
Forward Diode Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.5A, V <sub>G</sub> S=0V		-0.89	-1.2	V

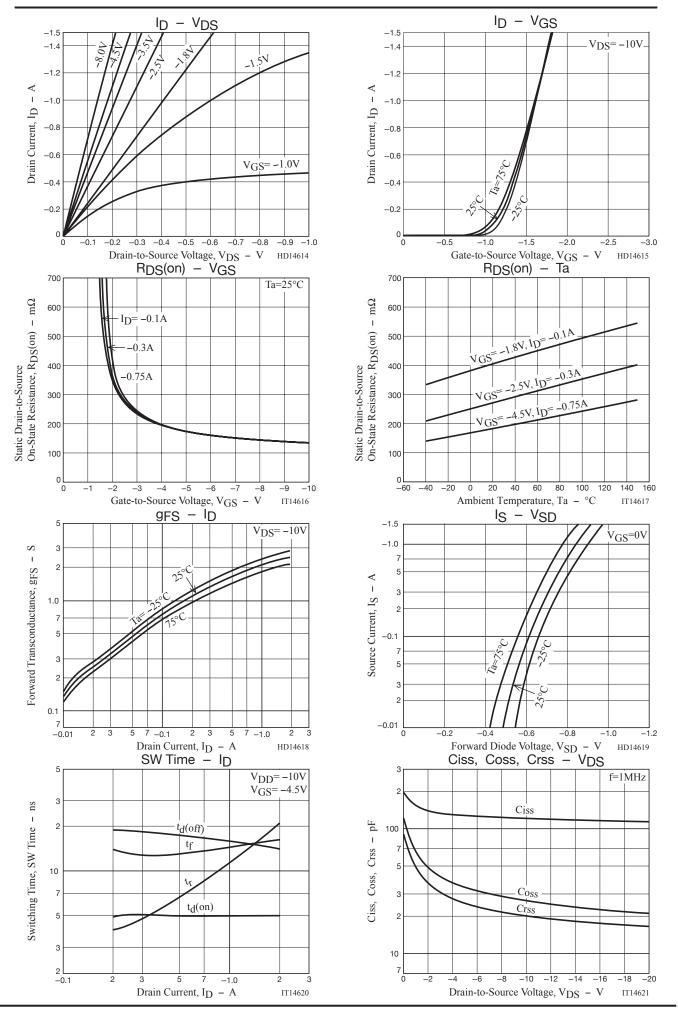
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# **Switching Time Test Circuit**

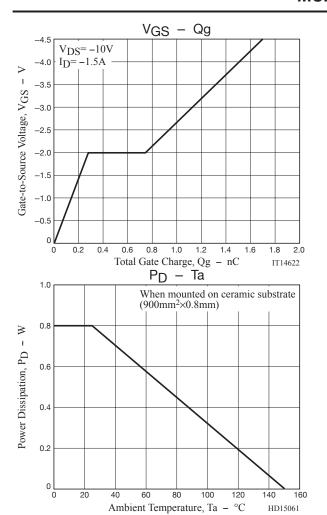


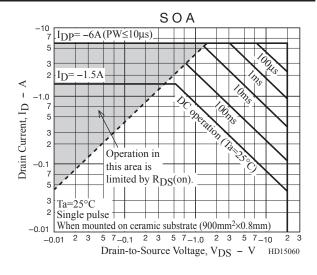
# **Ordering Information**

Device	Package	Shipping	memo	
MCH3376-TL-E	MCPH3	2.000mag/ragl	Pb-Free	
MCH3376-TL-W	IVICPH3	3,000pcs./reel	Pb-Free and Halogen Free	



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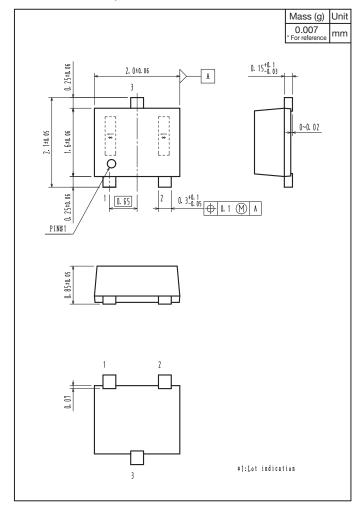


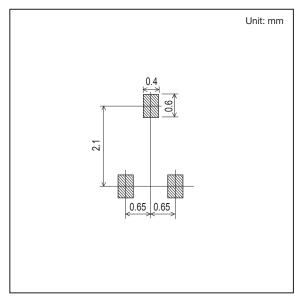


#### **Outline Drawing**

MCH3376-TL-E, MCH3376-TL-W

#### **Land Pattern Example**





Note on usage: Since the MCH3376 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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